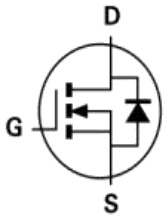
LT150N03AD

N-Channel Enhancement Mode MOSFET

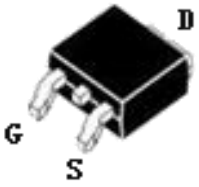
MAIN CHARACTERISTICS

I_D	150A
V_{DSS}	30V
RDSON-typ VGS=10V	2.55mΩ



FEATURES

• Adopt advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252

APPLICATIONS

• Battery protection
• Load switch
• Uninterruptible power supply

MECHANICAL DATA

• Case: Molded plastic
• Mounting Position: Any
• Molded Plastic: UL Flammability Classification Rating 94V-0
• Lead free in compliance with EU RoHS 2011/65/EU directive
• Solder bath temperature 275℃ maximum,10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LT150N03AD	TO-252	LT150N03AD	Tape

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Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	150	A
Pulsed Drain Current (Note1)	I_{DM}	600	A
Power Dissipation	P_D	110	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	360	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +175	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 250 μA	BV_{DSS}	30	-	-	V
Drain-Source Leakage Current	V_{DS} = 30 V, V_{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 250 μA	$V_{GS(th)}$	1.2	-	2.2	V
Drain-Source On-State Resistance	VGS=10V, ID=10A	RDS(on)	-	2.55	3	mΩ
	VGS=4.5V, ID=20A		-	4	6	mΩ
Forward Transconductance	V_{DS} = 5 V, I_D = 30 A	gfs	30	-	-	S
Input Capacitance	VDS=15V , VGS=0V , f=1MHz	C_{iss}	-	5100	-	pF
Output Capacitance		C_{oss}	-	1086	-	pF
Reverse Transfer Capacitance		C_{rss}	-	612	-	pF
Turn-on Delay Time(Note2)	VDD=15V , VGS=10V , RG=3Ω ID=30A	$t_{d(ON)}$	-	22	-	ns
Rise Time(Note2)		t_r	-	15	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	73	-	ns
Fall Time(Note2)		t_f	-	35	-	ns
Total Gate Charge(Note2)	VDS=15V , VGS=10V , ID=30A	Q_G	-	48	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	11	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	21	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	150	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	600	A
Drain-Source Diode Forward Voltage	VGS=0V , IS=1A , TJ=25℃	V_{SD}	-	-	1.2	V

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

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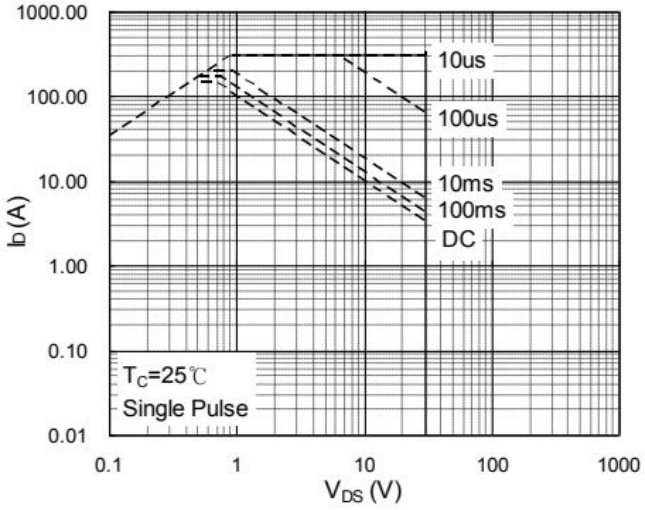
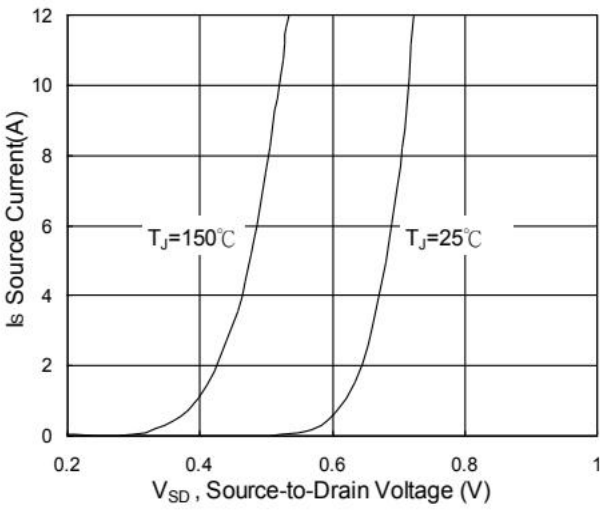
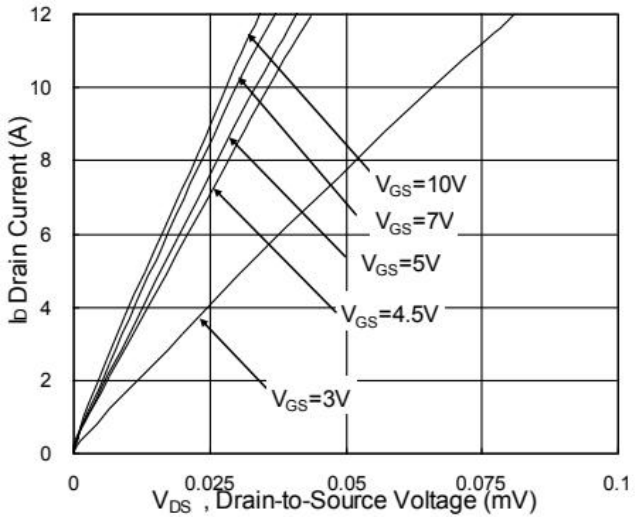
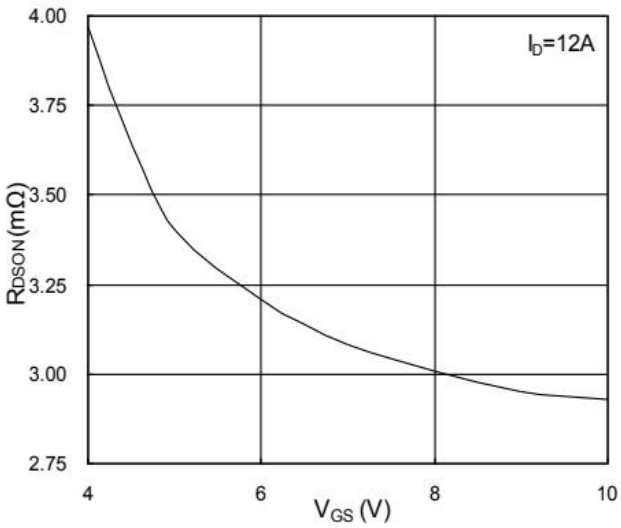
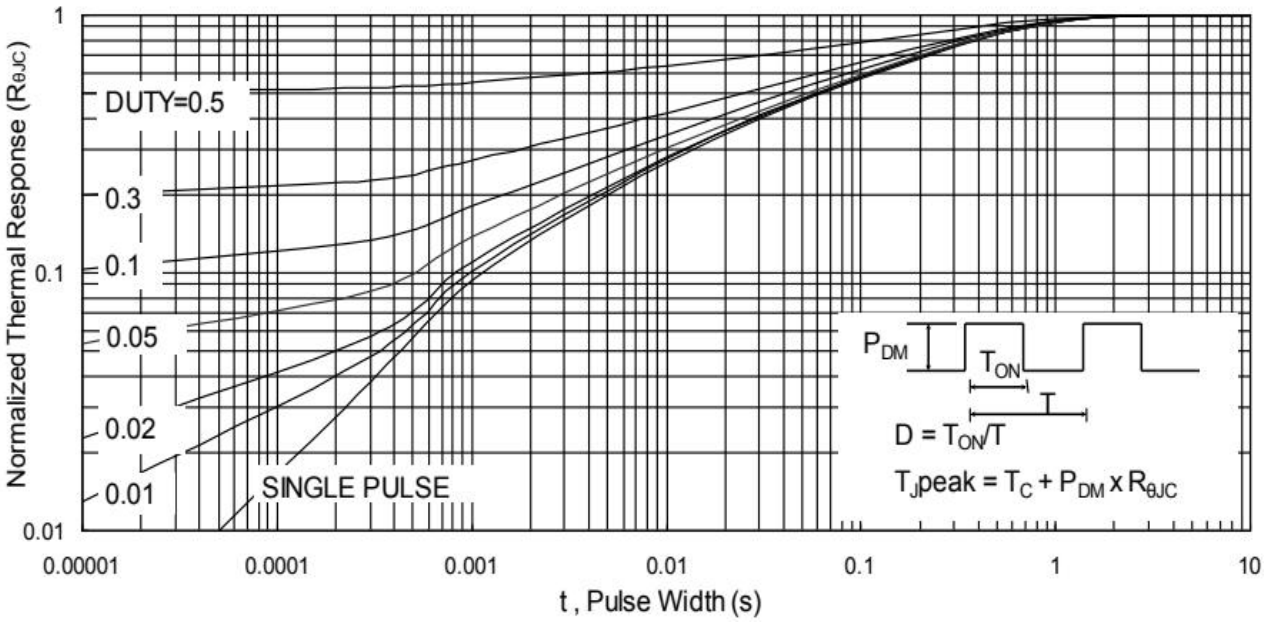
RATINGS AND CHARACTERISTIC CURVES











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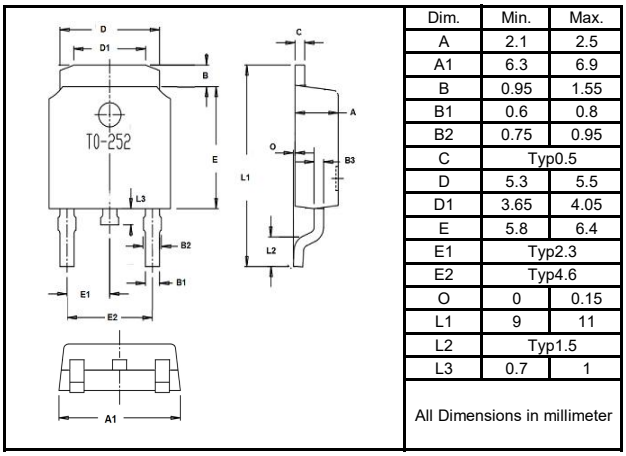
Package Outline Dimensions millimeters

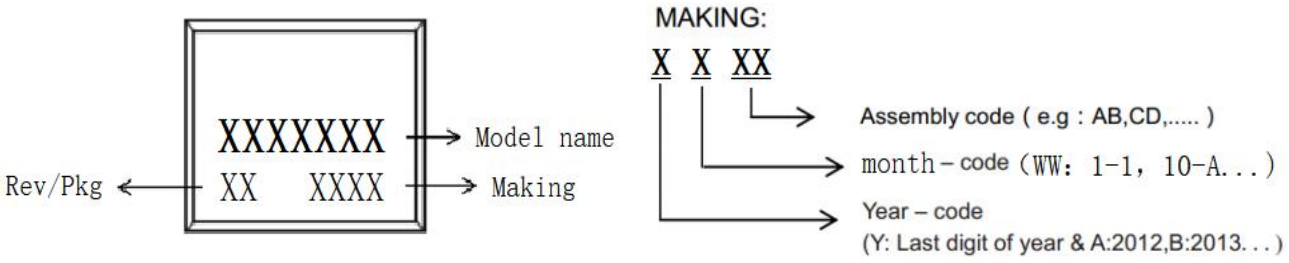
TO-252



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.95	1.55
B1	0.6	0.8
B2	0.75	0.95
C	Typ0.5	
D	5.3	5.5
D1	3.65	4.05
E	5.8	6.4
E1	Typ2.3	
E2	Typ4.6	
O	0	0.15
L1	9	11
L2	Typ1.5	
L3	0.7	1

All Dimensions in millimeter

Marking on the body



packing instruction

PKG	最小包装	内盒	外箱
TO-252			
	2500pcs/盘	5000pcs/盒	25000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal rated poer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.